

- ◇ General purpose diodes
- ◇ Fast switching devices
- ◇ **SOD323F Thin SMD package (Fig-1)**
- ◇ RoHS compliant / Green EMC
- ◇ Matte Tin (Sn) Lead finish
- ◇ Moisture Level Sensitivity 1
- ◇ Cathode Band / Device marking

Device Marking Code	
1N4148WS	S1
1N4448WS	S2
1N914BWS	S3

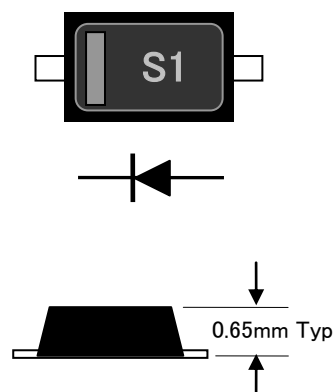


Fig.-1 Package. height

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Symbol	Parameter	Value	Units
V_{RSM}	Non-Repetitive Peak Reverse Voltage	100	V
V_{RRM}	Repetitive Peak Reverse Voltage	75	V
I_{FRM}	Repetitive Peak Forward Current	300	mA
I_{FSM}	Non-Repetitive Peak Forward Current ^{*1}	2	A
I_o	Continuous Forward Current	150	mA
P_D	Power Dissipation	200	mW
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{STG}	Storage Temperature	-55 to +150	$^\circ\text{C}$

^{*1} Pulse width = 1 μs

Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Symbol	Parameter	Conditions	Min	Max	Units
BV_R	Breakdown Voltage	$I_R = 100\ \mu\text{A}$	100		V
		$I_R = 5\ \mu\text{A}$	75		V
I_R	Reverse Current	$V_R = 20\text{V}$		25	nA
		$V_R = 75\text{V}$		5	μA
V_F	Forward Voltage	$I_F = 5\text{mA}$ ^{*2}	0.62	0.72	V
		$I_F = 10\text{mA}$		1	V
		$I_F = 100\text{mA}$ ^{*2}		1	V
C	Capacitance	$V_R = 0\text{V}, f = 1\text{MHz}$		4	pF
T_{RR}	Reverse Recovery Time	$I_F = 10\text{mA}, V_R = 6\text{V}$ $I_{RR} = 1\text{mA}, R_L = 100\ \Omega$		4	ns



Package Dimensions

